

PATENT
Any. Dkt. No.: AMAT/2966/DD/BCVD/1W

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:
Rathi et al.

Serial No.: 09/165,248

Confirmation No.: 7619

Filed: October 1, 1998

For: A SILICON CARBIDE
DEPOSITION AS A BARRIER
LAYER AND AN ETCH STOP

Group Art Unit: 2811

Examiner: G. Fourson

Assistant Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

CERTIFICATE OF MAILING	
37 CFR 1.8	
I hereby certify that this correspondence is being deposited on	
January 29, 2002, with the United States Postal Service as	
First Class Mail in an envelope addressed to: Assistant	
Commissioner for Patents, Washington, D.C. 20231.	
1/29/02	Kim R. Fisher
Date	Signature

RESPONSE TO FINAL OFFICE ACTION DATED NOVEMBER 29, 2001

In response to the Final Office Action dated November 29, 2001, having a shortened statutory period for response set to expire on February 28, 2002, please enter the following amendments and reconsider the claims pending in the application for reasons discussed below.

IN THE CLAIMS:

Please cancel claims 23-27 without prejudice, and amend the claims as follows:

- (Twice Amended) A method for processing a substrate, comprising:
depositing a silicon carbide barrier layer on the substrate by a method comprising:
introducing an alkylsilane and a noble gas into a chamber;
initiating a plasma in the chamber; and

Page 1

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